ISL71934M

Radiation Tolerant SP2T RF Switch, 50MHz to 10GHz

Description

The ISL71934M is a high reliability, low insertion loss, 50Ω SP2T absorptive RF switch designed for a multitude of wireless and other RF applications. This device covers a broad frequency range from 50MHz to 10GHz. In addition to providing low insertion loss, the ISL71934M delivers high linearity and high isolation performance while providing a 50Ω termination to the unused RF input port.

The ISL71934M uses a single positive supply voltage of 2.7V to 5.25V supporting three states using either 3.3V or 1.8V control logic.

Competitive Advantage

The ISL71934M provides the following advantages:

- Constant impedance $K_{|Z|}$ during switching transition
- Insertion loss = 0.7dB (at 2GHz)
- RFX to RFC isolation = 71dB (at 1GHz)
- IIP3 = +64dBm (at 1GHz)
- Active port operating power handling = 34dBm
- Term port operating power handling = 27dBm

Applications

- Satellite communications system
- Antenna switching
- IF switching
- Digital pre-distortion feedback

Features

- Qualified to Renesas Rad Tolerant Screening and QCI Flow (R34TB0004EU)
- High isolation:
  - 71dB at 1GHz
  - 60dB at 4GHz
- High linearity:
  - IIP2 of 111dBm
  - IIP3 of 64dBm at 1GHz
- Wide single 2.75V to 5.25V supply voltage range
- 3.3V and 1.8V compatible control logic
- Operating temperature: -55°C to +125°C
- 3x3mm 16-TQFN package
- Ni/Pd/Au lead finish (Tin (Sn)-free)
- TID Characterization (LDR: ≤10mrad(Si)/s): 30krad(Si)
- SEE Characterization
  - No DSEE with VDD = 6.2V at 43MeV•cm^2/mg
  - SET <10ns with F_{RF} = 10MHz at 43MeV•cm^2/mg
- Manufactured using SOI wafer fab process

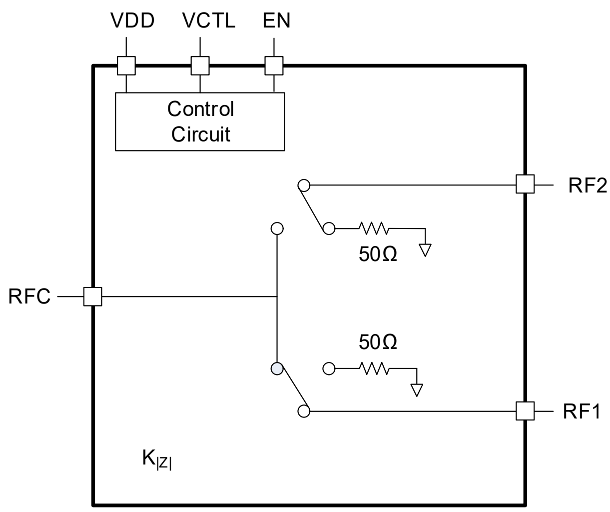


Figure 1. Block Diagram

Contents

1. Pin Information

1.1 Pin Assignments

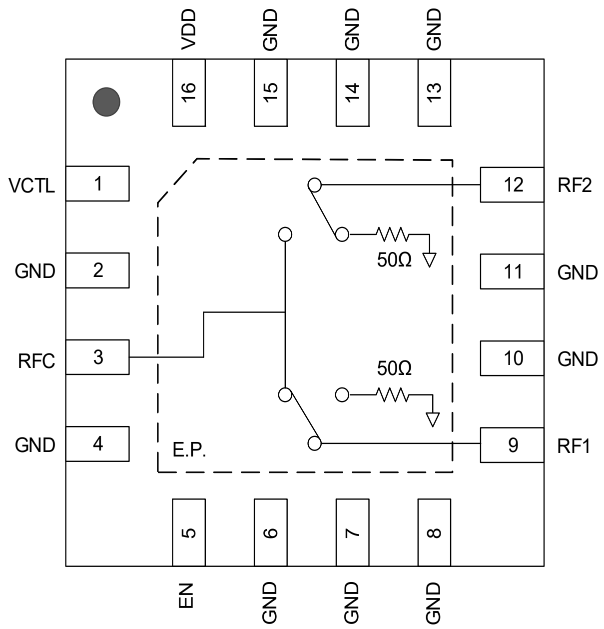


Figure 2. Pin Assignments - Top View

1.2 Pin Descriptions

Pin	Name	Function
1	VCTL	Controls the selected path when EN is low. It is disabled when EN is logic high (see Absolute Maximum Ratings). *Note*: VDD must be applied before or concurrently to voltage being applied to this pin.
3	RFC	RF Common Port. Matched to 50Ω when one of the two RF ports is selected. *Note*: If this pin is not 0V DC, an external coupling capacitor must be used.
2, 4, 6, 7, 8, 10, 11, 13, 14, 15	GND	Ground. Also, internally connected to the ground paddle. Ground this pin as close to the device as possible.
5	EN	EN as a logic low allows VCTL to control the selected switch path. With EN set to logic high puts the part in all paths off state and disables the control of VCTL (Absolute Maximum Ratings). *Note*: VDD must be applied before or concurrently to voltage being applied to this pin.
9	RF1	RF1 Port. Matched to 50Ω. *Note*: If this pin is not 0V DC, an external coupling capacitor must be used.
12	RF2	RF2 Port. Matched to 50Ω. *Note*: If this pin is not 0V DC, an external coupling capacitor must be used.
16	VDD	Power Supply. Bypass to GND with capacitors shown in the Typical Application Circuit as close as possible to pin.
	EP	Exposed Pad. Internally connected to GND. Solder this exposed pad to a PCB pad that uses multiple ground vias to provide heat transfer out of the device and into the PCB ground planes. These multiple ground vias are also required to achieve the specified RF performance.

2. Specifications

2.1 Absolute Maximum Ratings

Caution: Do not operate at or near the maximum ratings listed for extended periods of time. Exposure to such conditions can adversely impact product reliability and result in failures not covered by warranty.

Parameter/Condition		Symbol	Minimum	Maximum	Unit
VDD to GND		V_{DD}	-0.3	+5.5	V
VCTL, EN to GND		V_{logic}	-0.3	3.6	V
RF1, RF2, RFC to GND		V_{RF}	-0.3	+0.3	V
RF Input Power[1]	RF1 or RF2 as an input (Connected to RFC)	P_{RF12}	-	36	dBm
	RFC as an input (Connected to RF1 or RF2)	P_{RFC}	-	36	dBm
	RFC as an input (All off state)	P_{RFC_OFF}	-	30	dBm
	RF1 or RF2 as input (Terminated states)	P_{RF12_TERM}	-	30	dBm
	RF1 and RF2 as inputs (All off state)	P_{RF12_OFF}	-	30[2]	dBm
Human Body Model (Tested per JESD22-A114)		V_{ESDHBM}	-	1.5	kV
Charged Device Model (Tested per JESD22-C101)		V_{ESDCDM}	-	2	kV

1. V_{DD} = 2.7V to 5.25V, 250MHz ≤ F_{RF} ≤ 10GHz, T_C = 105°C, Z_S = Z_L = 50Ω.
2. Each port.

2.2 Thermal Information

Thermal Resistance (Typical)	θ_{JA} (°C/W)[1]	θ_{JC} (°C/W)[2]
16 Ld TQFN	59	17

1. θ_{JA} is measured in free air with the component mounted on a high-effective thermal conductivity test board with direct attach features. See TB379.
2. For θ_{JC}, the case temperature location is the center of the exposed metal pad on the package underside.

Parameter	Minimum	Maximum	Unit
Maximum Junction Temperature (T_{JMAX})		+125	°C
Storage Temperature Range (T_{ST})	-65	+150	°C
Pb-Free Reflow Profile	See TB493		

2.3 Recommended Operating Conditions

Parameter	Symbol	Condition		Minimum	Typical	Maximum	Units
Supply Voltage	V_{DD}	-		2.7	-	5.25	V
Operating Temperature Range	T_{CASE}	Exposed Paddle Temperature		-55	-	+125	°C
RF Frequency Range	F_{RF}	-		0.05	-	10	GHz
RF Continuous Input CW Power (Non-Switched)[1]	P_{RF}	RFC connected to RF1 or RF2[2]		-	-	34	dBm
		RF1/ RF2 Input, Terminated State[3][4]		-	-	27	dBm
		RFC Input, All off State		-	-	27	dBm
RF Continuous Input Power (RF Hot Switching CW)[1]	P_{RFSW}	RFC Input, switching between RF1 and RF2.	T_C = 85 °C	-	-	30	dBm
			T_C = 105 °C	-	-	30	dBm
		RFC Input, switching into or out of, All off State.	T_C = 85 °C	-	-	27	dBm
			T_C = 105 °C	-	-	27	dBm
		RF1 or RF2 as input, switched between RFC and Term.	T_C = 85 °C	-	-	27	dBm
			T_C = 105 °C	-	-	27	dBm
		RF1 and RF2 as inputs, switching into or out of All off State.[4]	T_C = 85 °C	-	-	27	dBm
			T_C = 105 °C	-	-	27	dBm
RF1/2 Port Impedance	Z_{RFx}	-		-	50	-	Ω
RFC Port Impedance	Z_{RFC}	-		-	50	-	Ω

1. Levels based on: V_{DD} = 3.1V to 5.25V, 250MHz ≤ F_{RF} ≤ 10GHz, Z_S = Z_L = 50Ω. See Figure 3 for power handling derating vs. RF frequency.
2. Input could be: RFC, RF1, or RF2 (applied to only one input).
3. Any RF1 / RF2 termination state. Power level specified is for each port.
4. Power level specified is for each port.

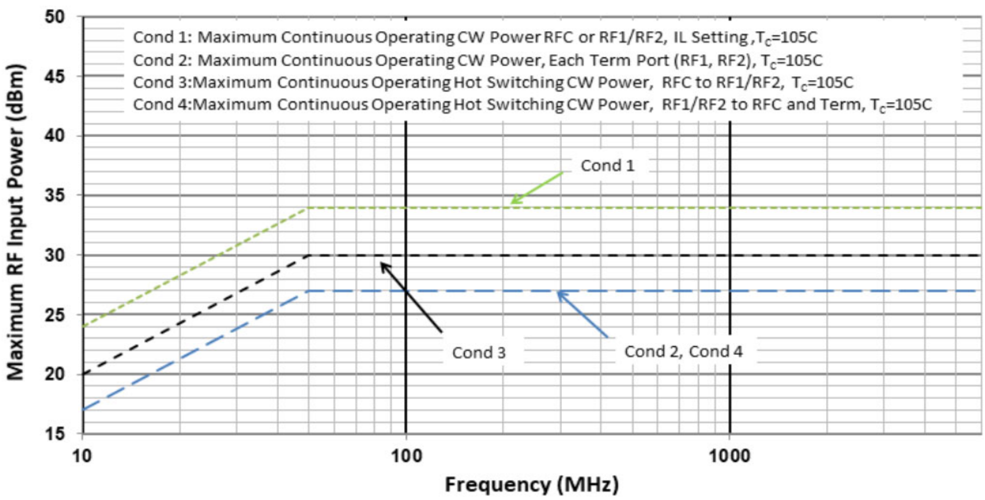


Figure 3. Maximum RF Input Operating Power vs. Frequency

2.4 Electrical Specifications

Typical Application Circuit, V_{DD} = 5.0V, T_C = +25°C, F_{RF} = 2000MHz, Driven Port = RF1 or RF2, input power = 0dBm, ZS = ZL = 50Ω, PCB board trace and connector losses are de-embedded unless otherwise noted. **Boldface limits apply across the operating temperature range, -55°C to +125°C by characterization with production testing at +25°C.**

Parameter	Symbol	**Condition**	Minimum[1][2]	Typical	Maximum[1][2]	Units
Logic Input High Threshold	V_{IH}		**1.1**	-	**3.6**	V
Logic Input Low Threshold	V_{IL}		**-0.3**	-	**0.6**	V
Logic Current	I_{IH}, I_{IL}	For each control pin	**-1**	-	**+1**	µA
DC Current	I_{DD}	V_{DD} = 3.3 V	-	200	**400**	µA
		V_{DD} = 5.0 V	-	260	**450**	µA
Insertion Loss RFC to RF1 / RF2	IL	50MHz	-	0.7	-	dB
		1GHz	-	0.7	-	dB
		2GHz	-	0.7	**1.1**	dB
		3GHz	-	0.7	-	dB
		4GHz	-	0.7	-	dB
		6GHz	-	0.8	-	dB
		8GHz	-	1.0	-	dB
		10GHz	-	1.2	-	dB
Isolation RFC to RF1 / RF2	ISOC	50MHz	76	79	-	dB
		1GHz	67	71	-	dB
		2GHz	62	66	-	dB
		3GHz	61	64	-	dB
		4GHz	58	60	-	dB
		6GHz	47	51	-	dB
		8GHz	-	43	-	dB
		10GHz	-	35	-	dB
Isolation RF1 to RF2	ISOX	50MHz	-	72	-	dB
		1GHz	-	62	-	dB
		2GHz	-	56	-	dB
		3GHz	-	52	-	dB
		4GHz	-	50	-	dB
		6GHz	-	44	-	dB
		8GHz	-	40	-	dB
		10GHz	-	32	-	dB
Return Loss RFC	RFC_{RL}	50MHz	-	25	-	dB
		1GHz	-	25	-	dB
		2GHz	-	24	-	dB
		3GHz	-	23	-	dB
		4GHz	-	25	-	dB
		6GHz	-	24	-	dB
		8GHz	-	17	-	dB
		10GHz	-	12	-	dB

Typical Application Circuit, V_{DD} = 5.0V, T_C = +25°C, F_{RF} = 2000MHz, Driven Port = RF1 or RF2, input power = 0dBm, ZS = ZL = 50Ω, PCB board trace and connector losses are de-embedded unless otherwise noted. **Boldface limits apply across the operating temperature range, -55°C to +125°C by characterization with production testing at +25°C.** (Cont.)

Parameter	Symbol	Condition		Minimum[1][2]	Typical	Maximum[1][2]	Units
Return Loss RF1, RF2 On State, EN = 0	$RFON_{RL}$	50MHz		-	25	-	dB
		1GHz		-	26	-	dB
		2GHz		-	27	-	dB
		3GHz		-	24	-	dB
		4GHz		-	23	-	dB
		6GHz		-	26	-	dB
		8GHz		-	18	-	dB
		10GHz		-	13	-	dB
Return Loss RF1, RF2 Off State, EN = 0	$RFOFF_{RL}$	50MHz		-	39	-	dB
		1GHz		-	32	-	dB
		2GHz		-	40	-	dB
		3GHz		-	32	-	dB
		4GHz		-	25	-	dB
		6GHz		-	25	-	dB
		8GHz		-	33	-	dB
		10GHz		-	27	-	dB
Input 0.1dB Compression	$IP_{0.1dB}$	V_{DD} = 5.0 V	50MHz	-	30	-	dBm
			2GHz	-	32	-	dBm
			3GHz	-	32	-	dBm
			4GHz	-	32	-	dBm
			6GHz	-	34	-	dBm
			8GHz	-	33	-	dBm
			10GHz	-	32	-	dBm
		V_{DD} = 3.1 V	50MHz	-	30	-	dBm
			2GHz	-	32	-	dBm
			3GHz	-	32	-	dBm
			4GHz	-	32	-	dBm
			6GHz	-	34	-	dBm
			8GHz	-	33	-	dBm
			10GHz	-	32	-	dBm
Input IP2	IIP2	F_{RF1} = 2000MHz, F_{RF2} = 1990MHz RFIN = RF1 or RF2 PIN = +20dBm / tone $F_{IP2} = F_{RF1} + F_{RF2}$		-	111	-	dBm
Input IP3	IIP3	RF Input = RF1 or RF2 PIN = +15 dBm/tone Δ F = 1MHz	50MHz	-	58	-	dBm
			1GHz	-	64	-	dBm
			2GHz	-	64	-	dBm
			2.5GHz	-	63	-	dBm
			4GHz	-	63	-	dBm
			6GHz	-	64	-	dBm
			8GHz	-	64	-	dBm
			10GHz	-	61	-	dBm

Typical Application Circuit, V_{DD} = 5.0V, T_C = +25°C, F_{RF} = 2000MHz, Driven Port = RF1 or RF2, input power = 0dBm, ZS = ZL = 50Ω, PCB board trace and connector losses are de-embedded unless otherwise noted. **Boldface limits apply across the operating temperature range, -55°C to +125°C by characterization with production testing at +25°C.** (Cont.)

Parameter	Symbol	Condition	Minimum[1][2]	Typical	Maximum[1][2]	Units
Non-RF Driven Spurious[3]	$Spur_{MAX}$	At any RF port when externally terminated into 50Ω	-	-114	-	dBm
Switching Time[4]	T_{SW}	50% control to 90% RF	-	325	-	ns
		50% control to 10% RF	-	255	-	ns
Maximum Switching Rate[5]	SW_{RATE}	-	-	25	-	kHz

1. Items in minimum/maximum columns in bold are established by Test.
2. Items in minimum/maximum columns that are not bold are established by Design Characterization.
3. Spurious due to on-chip negative voltage generator. Typical generator fundamental frequency is 5.2MHz.
4. F_{RF} = 1GHz.
5. Minimum time required between switching of states = 1 / Maximum Switching Rate.

2.5 Control Mode

Table 1. Switch Control Truth Table

VCTL	EN	RFC to RF1	RFC to RF2
0	0	OFF	ON
1	0	ON	OFF
0	1	OFF	OFF
1	1	OFF	OFF

3. Typical Performance Graphs

V_{DD} = 3.3V or 5.0V, T_C = +25°C (T_C = Temperature of Exposed Paddle), F_{RF} = 2000MHz, Z_S = Z_L = 50Ω, P_{IN} = +0dBm for all small signal tests, RFC is the driven port and RF1 or RF2 is the output port, all unused RF ports terminated into 50Ω, unless otherwise specified

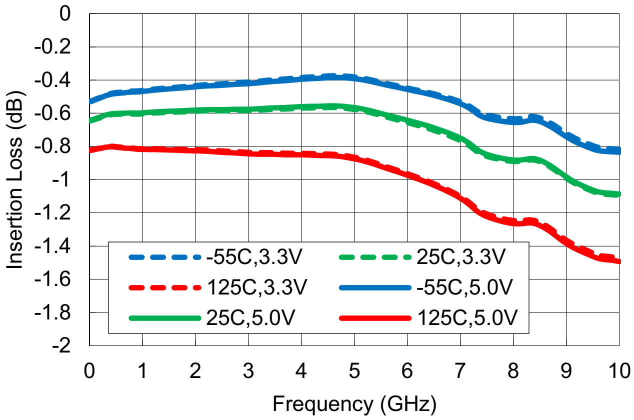


Figure 4. RFC to RF1 Insertion Loss

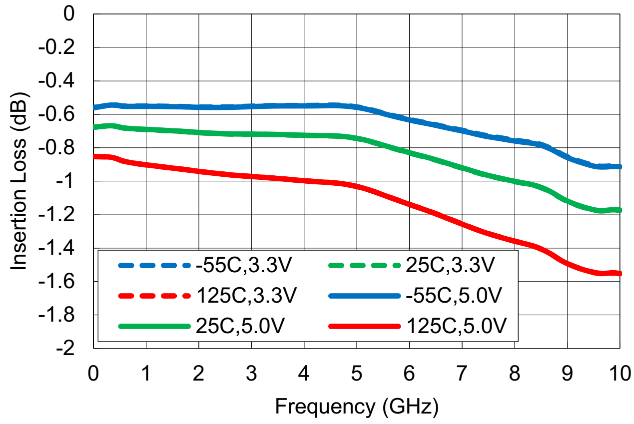


Figure 5. RFC to RF2 Insertion Loss

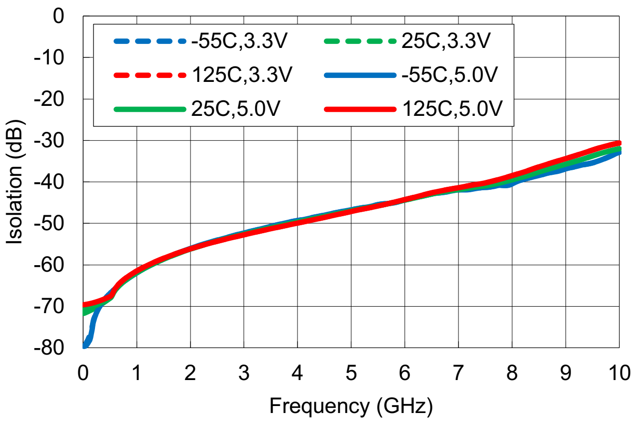


Figure 6. RF1 to RF2 to Isolation [RF2 Enabled]

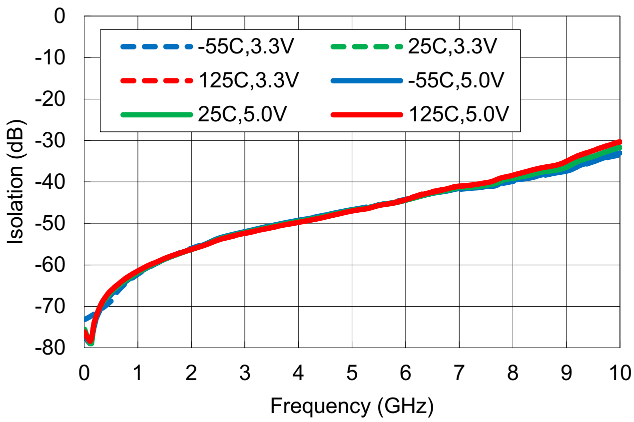


Figure 7. RF2 to RF1 Isolation [RF1 Enabled]

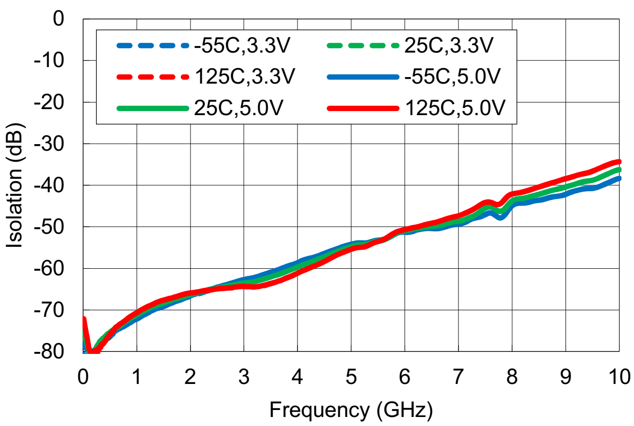


Figure 8. RF1 to RFC Isolation [RF2 Enabled]

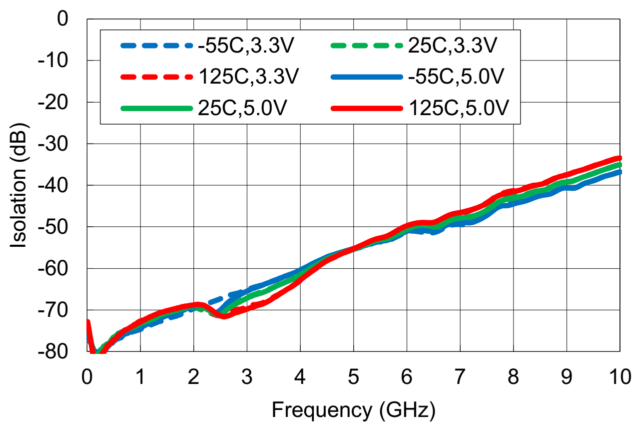


Figure 9. RF2 to RFC Isolation [RF1 Enabled]

V_{DD} = 3.3V or 5.0V, T_C = +25°C (T_C = Temperature of Exposed Paddle), F_{RF} = 2000MHz, Z_S = Z_L = 50Ω, P_{IN} = +0dBm for all small signal tests, RFC is the driven port and RF1 or RF2 is the output port, all unused RF ports terminated into 50Ω, unless otherwise specified (Cont.)

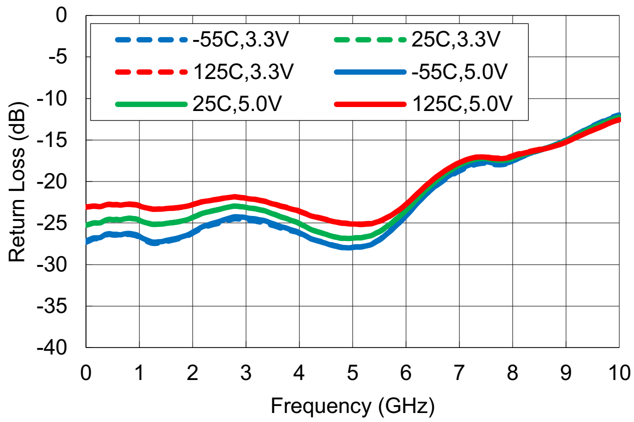


Figure 10. RFC Return Loss [RF1 Enabled]

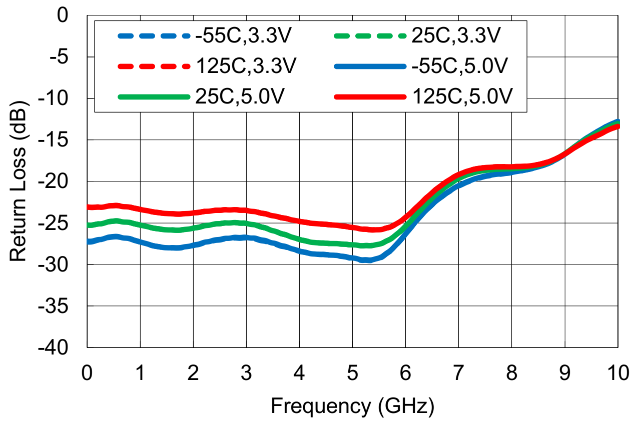


Figure 11. RFC Return Loss [RF2 Enabled]

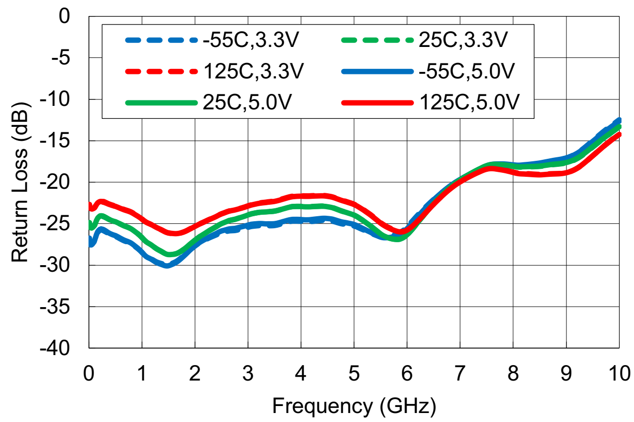


Figure 12. RF1 Return Loss [RF1 Enabled]

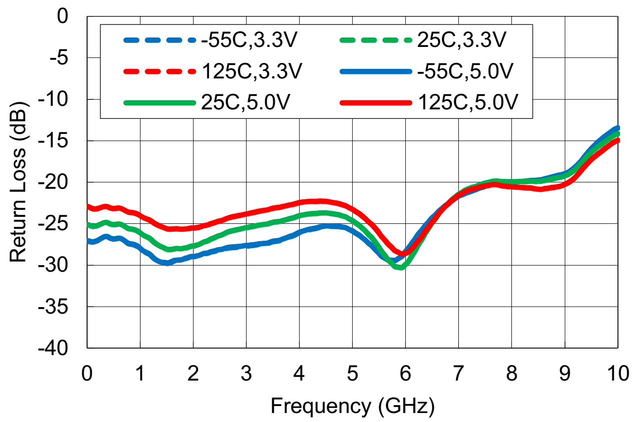


Figure 13. RF2 Return Loss [RF2 Enabled]

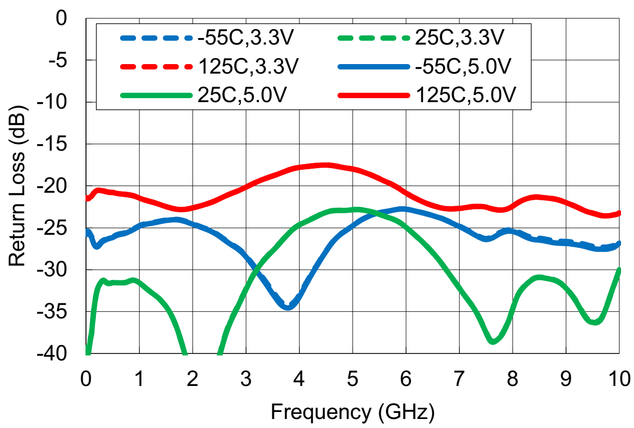


Figure 14. RF1 Return Loss [RF1 Off]

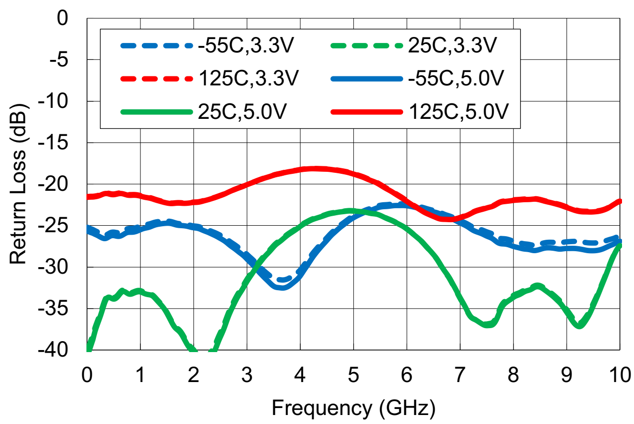


Figure 15. RF2 Return Loss [RF2 Off]

4. Applications Information

4.1 Default Start-up

There are no internal pull-up or pull-down resistors on the VCTL or EN pins.

4.2 Logic Control

Control pins VCTL and EN are used to set the state of the SP2T switch (see Absolute Maximum Ratings).

4.3 Power Supplies

Use a common V_{CC} power supply for all pins requiring DC power. Bypass all supply pins with external capacitors to minimize noise and fast transients. Supply noise can degrade noise figures and fast transients can trigger ESD clamps and cause them to fail. Supply voltage change or transients should have a slew rate smaller than 1V/20µs. In addition, keep all control pins at 0V (±0.3V) while the supply voltage ramps or while it returns to zero.

4.4 Control Pin Interface

If control signal integrity is a concern and clean signals cannot be ensured because of issues such as overshoot, undershoot, and ringing, the following circuit at the input of each control pin is recommended. This applies to control Pin 1 (VCTL) and Pin 5 (EN) as shown in Figure 16.

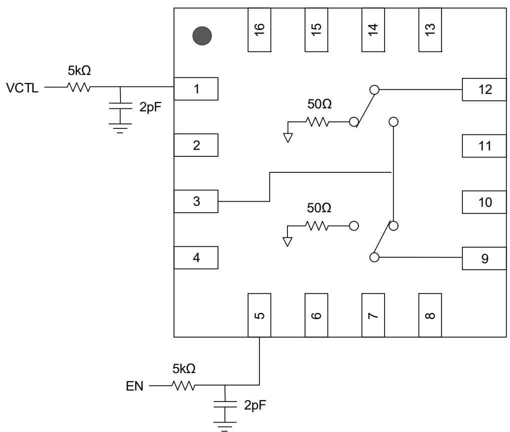


Figure 16. Typical Application Circuit

4.5 Cold Sparing

4.5.1 Setup and Test Conditions

The cold sparing test is intended to verify performance of the part when the part is unpowered while still having a large RF input power applied. The parts were tested under three conditions:

- Condition 1: V_{DD} is off and floating. (Units 25A, 26A, and 27A)
- Condition 2: V_{DD} is off and grounded. (Units 25B, 26B, and 27B)
- Condition 3: The part is powered on at 5V and in disable mode (RFC-RF1 and RFC-RF2 paths are isolated). (Units 25C, 26C, and 27C)

For each condition, an input power of 30dBm was applied at a frequency of 50MHz to the RFC port. The RF1 and RF2 ports are terminated with 50Ω loads. Three parts were tested under each condition for a 24 hour period. Before each test, the supply current was measured along with the s-parameters. After each test, the supply current was measured along with the s-parameters.

4.5.2 Results

There were no noticeable changes in the s-parameters between the pre-test data and the post-test data. Table 2 shows the pre-test and post-test supply currents. The are no noticeable changes in supply current.

Table 2. Cold Sparing Supply Current Results

Unit	Pre-Test (mA) (V_{DD} = 5V)	Post-Test (mA) (V_{DD} Floating	Post-Test (mA) (V_{DD} Grounded)	Post-Test (mA) (5V and Disabled)
25A	0.228	0.228	-	-
26A	0.233	0.233	-	-
27A	0.227	0.227	-	-
25B	0.241	-	0.241	-
26B	0.232	-	0.232	-
27B	0.229	-	0.230	-
25C	0.229	-	-	0.229
26C	0.218	-	-	0.218
27C	0.223	-	-	0.223

5. Radiation Tolerance

The ISL71934M is a radiation tolerant device for commercial space applications, Low Earth Orbit (LEO) applications, high altitude avionics, launch vehicles, and other harsh environments. The response of the device to Total Ionizing Dose (TID) radiation effects and Single-Event Effects (SEE) has been measured, characterized, and reported in the following sections. However, TID performance is not guaranteed through radiation acceptance testing.

5.1 Total Ionizing Dose (TID) Testing

5.1.1 Introduction

To determine the sensitivity of the ISL71934M to the total dose environment, the TID test was conducted. Test downpoints were 0krad(Si), 10krad(Si), 20krad(Si), and 30krad(Si). Total dose testing was performed using a Hopewell Designs N40 panoramic 60Co irradiator. The irradiations were performed at a dose rate of 0.00875rad(Si)/s. A PbAl box shielded the test fixture and devices under test against low energy secondary gamma radiation. The characterization matrix consisted of 18 samples irradiated under bias and 18 samples irradiated with all pins grounded. All electrical testing was performed outside the irradiator using Automated Test Equipment (ATE) with data logging at each downpoint. Downpoint electrical testing was performed at room temperature.

The bias configuration is shown in Figure 17.

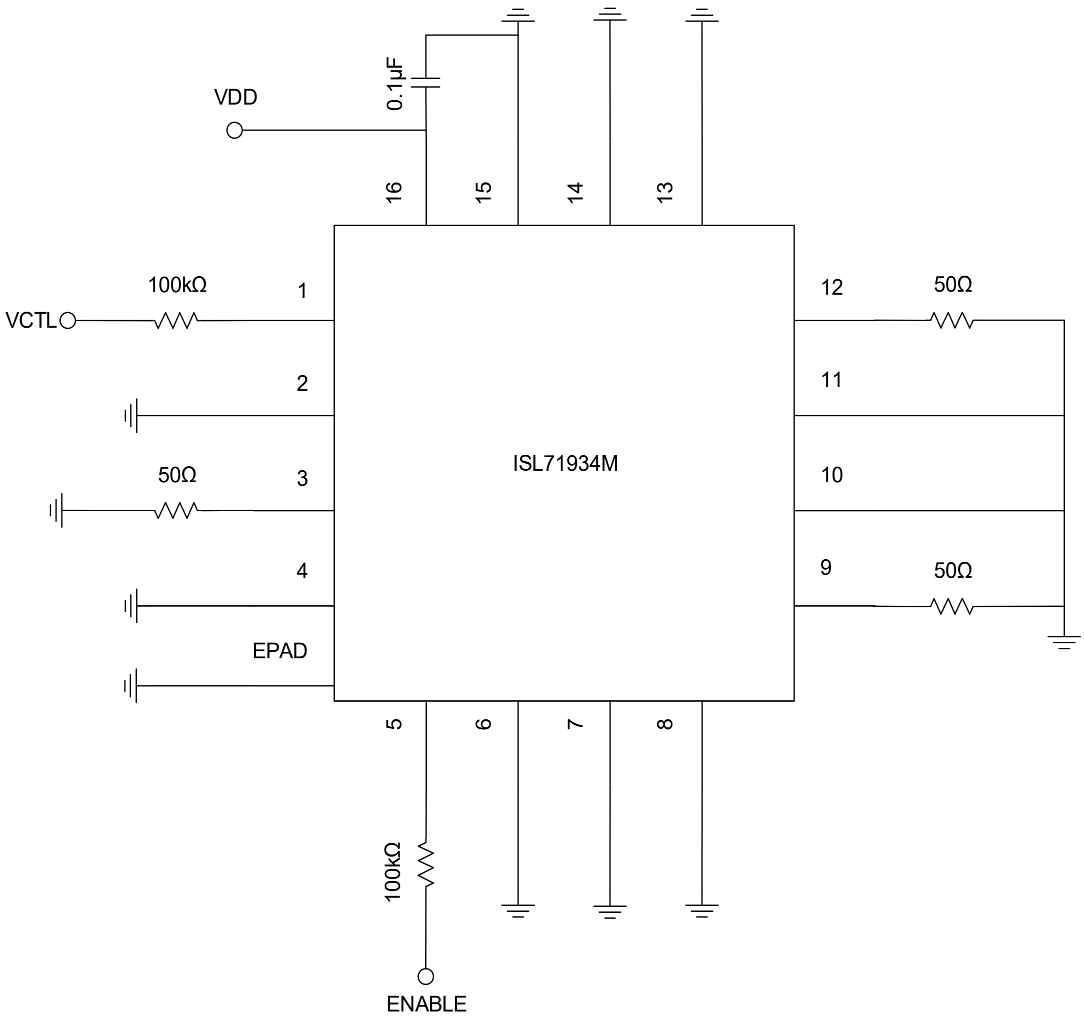


Figure 17. Bias Configuration

5.1.2 TID Results

Figure 18 through Figure 21 show the performance parameters for key specifications over TID.

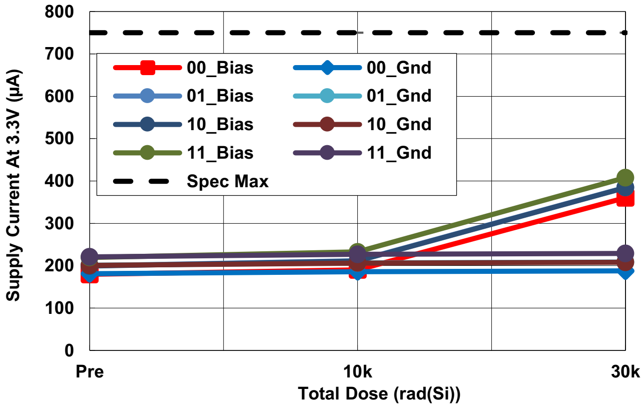


Figure 18. I_{DD} for V_{DD} = 3.3V vs TID

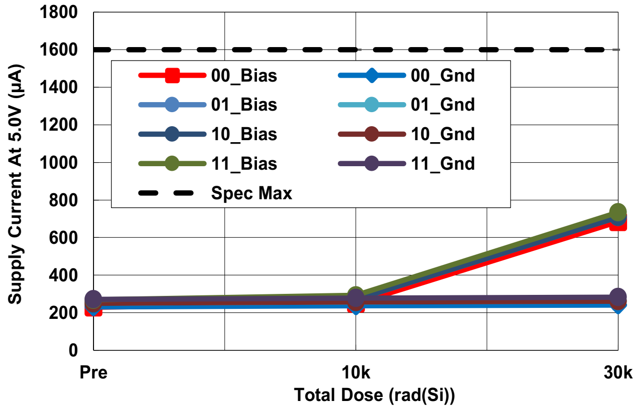


Figure 19. I_{DD} for V_{DD} = 5V vs TID

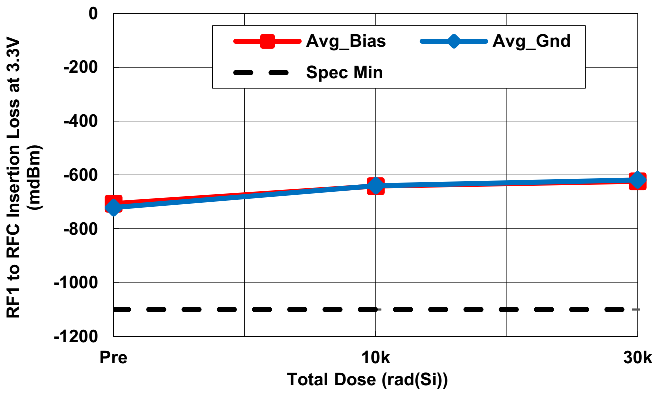


Figure 20. Insertion Loss RF1 to RFC at 2GHz and V_{DD} = 3.3V vs TID

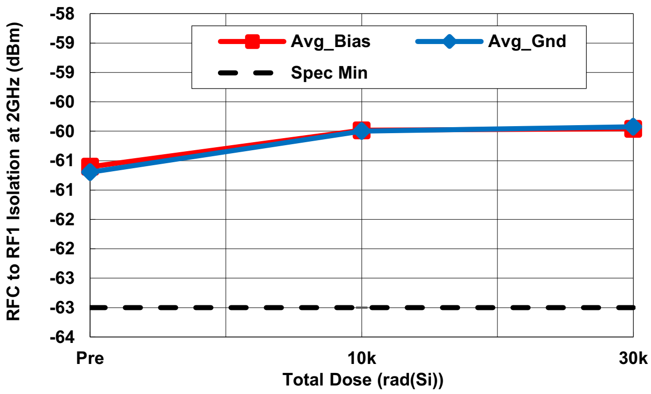


Figure 21. RFC to RF1 Isolation at 2GHz and V_{DD} = 3.3V vs TID

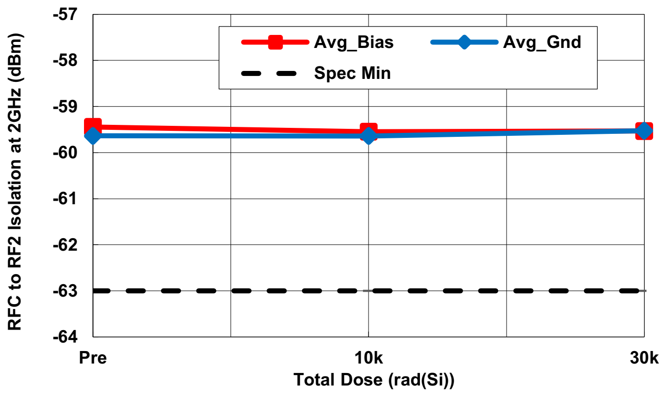


Figure 22. RFC to RF2 Isolation at 2GHz and V_{DD} = 3.3V vs TID

5.2 Single-Event Effects Testing

The intense heavy ion environment encountered in space applications can cause a variety of Single-Event Effects (SEE). SEE can lead to system-level performance issues, including disruption, degradation, and destruction. For predictable and reliable space system operation, characterize individual electronic components to determine their SEE response. The following is a summary of the ISL71934M SEE testing.

5.2.1 SEE Test Facility

Testing was performed at Texas A&M University (TAMU Cyclotron Institute heavy ion facility. The overall test setup includes the test jig containing the evaluation cards mounted and wired through 20ft cable to the data room. The input pins RFC, RF1, and RF2 were connected with a series 10µF capacitor to ensure that only AC signals were applied to the ISL71934M. The power and control pins VDD, VCLT, and EN all had a 1µF decoupling capacitor to ground to minimize noise.

5.2.2 SEE Test Setup

For SEB and SEL testing, VDD was set to 5.5V, 5.8V, 6.2V, and 6.8V. The RFC pin was stimulated using a 10MHz signal with a peak amplitude of ±5V (24dBm). The inputs VCLTL and EN were set to 2.5V so that all three RF inputs were open. The supply current through the VDD pin was monitored to look for increases because of radiation.

5.2.3 Single Event Burnout and Latch-Up (SEB/L) Results

No SEB was observed for the device LET of 43MeV·cm^2/mg (+125°C) for V_{DD} = 5.5V, 5.8V, and 6.2V. Runaway currents were observed for 1 DUT at V_{DD} = 6.5V. For V_{DD} = 5.5V, 5.8V, and 6.2V, no current increases were seen outside of ±2%.

5.2.4 SET Results

The SET testing was performed with VCTL = 1.1V (logic 1) and EN = 0V (logic 0). This enables the connection from the RFC to RF1 pins, with minimal margin on the digital control pins. A 10MHz, ±5V peak sine wave was applied to RFC. Both RF1 and RF2 were monitored using an oscilloscope. The oscilloscope was set to trigger on a ±10ns deviation in zero crossings. The part was operated at V_{DD} = 2.7V and 4.5V. The oscilloscope did not trigger on any of the four parts tested, indicating no SET events.

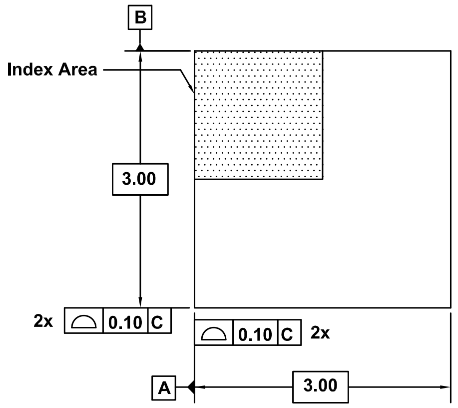
5.2.5 Conclusion

The ISL71934M shows no sensitivity to SEB/L or exhibits any SET for the full supply voltage range, including margin up to V_{DD} = 6.2V under the condition of LET value of 43MeV·cm^2/mg.

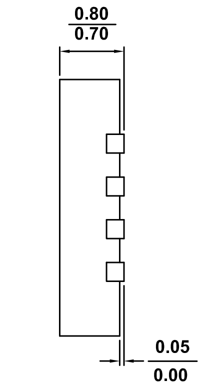
6. Package Outline Drawing

For the most recent package outline drawing, see L16.3x3F.

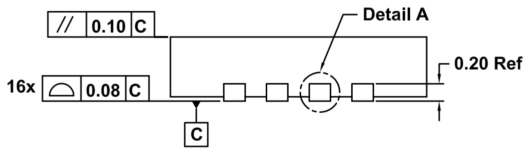
L16.3x3F
16 Lead Thin Quad Flat No-Lead Package
Rev 0, 2/20



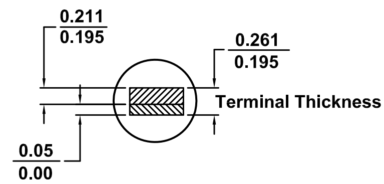
Top View



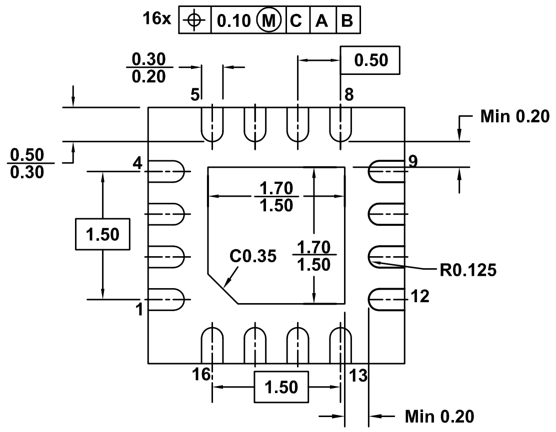
Side View



Side View



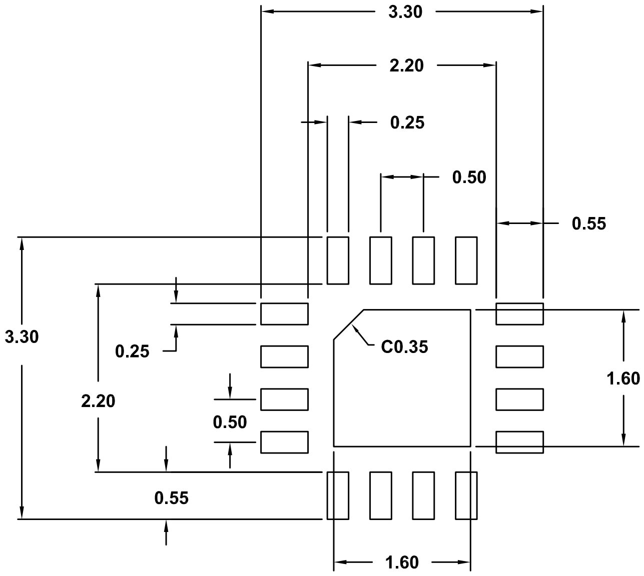
Detail A



Bottom View

Notes :

1. All dimensions are in mm. Angles are in degrees.
2. Coplanarity applies to the exposed pad and the terminals.
   Coplanarity shall not exceed 0.05mm.
3. Warpage shall not exceed 0.05mm.
4. The package length and package width are considered as special characteristics.
5. See JEDEC MO-220.



Recommended Land Pattern Dimension

Notes:

1. All dimensions are in mm. Angles are in degrees.
2. Top down view. As viewed on PCB.
3. Land pattern recommendation per IPC-7351B generic requirement for surface mount design and land pattern.

7. Ordering Information

Part Number[1]	Part Marking	LDR	Package Description (RoHS Compliant)	Pkg. Dwg. #	MSL Rating[2]	Carrier Type[3]	Temp. Range
ISL71934MRTZ	71934	30krad(Si)	16 Ld TQFN	L16.3x3F	1	Tray	-55 to +125°C
ISL71934MRTZ-T						Reel, 1k	

1. These Pb-free plastic packaged products employ special Pb-free material sets; molding compounds/die attach materials and NiPdAu plate - e4 termination finish, which is RoHS compliant and compatible with both SnPb and Pb-free soldering operations. Pb-free products are MSL classified at Pb-free peak reflow temperatures that meet or exceed the Pb-free requirements of IPC/JEDEC J-STD-020.
2. For more information about Moisture Sensitivity Level (MSL), see TB363.
3. See TB347 for details about reel specifications.

8. Revision History

Rev.	Date	Description
1.04	Feb 4, 2026	Added Cold Sparing section.
1.03	Nov 6, 2025	▪ Updated TID Features bullet. ▪ Added Boldface statement to EC table.
1.02	May 19, 2025	▪ Updated page 1 content. ▪ Updated Note 1 in Abs Max section. ▪ Updated the RF Frequency Range spec units from MHz to GHz and the max spec from 6000MHz to 10GHz. ▪ Updated Note 1 in the Recommended Operating Conditions table. ▪ Updated the following typical values in the Electrical Specifications table: • Insertion Loss • Isolation • Return Loss • Input 0.1dB Compression ▪ Added more conditions to Input IP3 specification. ▪ Removed Input 1dB Compression spec and applicable note. ▪ Updated Typical Performance Graphs to show extended frequency. ▪ Updated Note 1 in ordering table.
1.01	Feb 24, 2021	Updated the Ordering Information table and moved it to the end to follow new formatting.
1.00	Dec 4, 2020	Initial release

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